

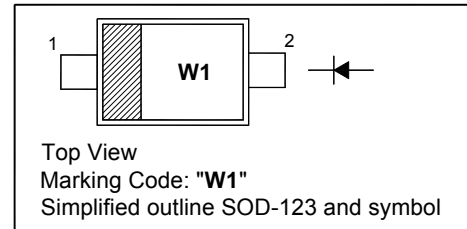
# 1N914W-13

## Silicon Epitaxial Planar Switching Diode

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

Note: Part number suffix: "-13" - 13 inch reel



### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Repetitive Reverse Voltage	$V_{RRM}$	100	V
Average Rectified Forward Current	$I_{F(AV)}$	215	mA
Non-repetitive Peak Forward Surge Current	$I_{FSM}$	1 2	A
		at $t = 1\text{ s}$ at $t = 1\ \mu\text{s}$	
Power Dissipation	$P_{tot}$	400	mW
Thermal Resistance from Junction to Ambient Air	$R_{\theta JA}$	312	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 5\ \mu\text{A}$ at $I_R = 100\ \mu\text{A}$	$V_{(BR)R}$	75 100	- -	V
Forward Voltage at $I_F = 10\text{ mA}$	$V_F$	-	1	V
Reverse Current at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 20\text{ V}$ , $T_j = 150^\circ\text{C}$	$I_R$	- - -	25 5 50	nA $\mu\text{A}$ $\mu\text{A}$
Capacitance at $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$	$C_{tot}$	-	4	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$ to $I_R = 1\text{ mA}$ , $V_R = 6\text{ V}$ , $R_L = 100\ \Omega$	$t_{rr}$	-	4	ns

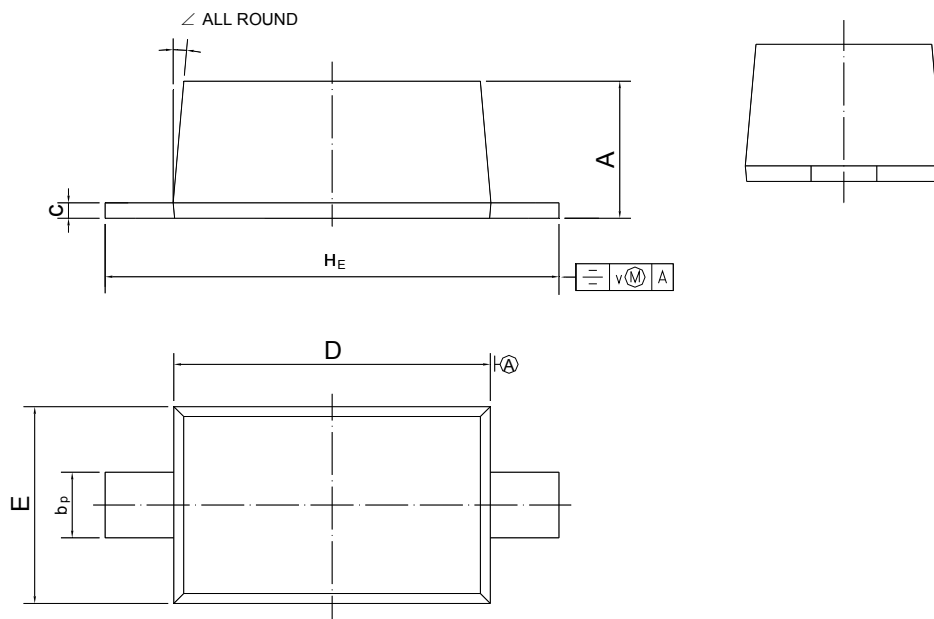
**TOP DYNAMIC**

# 1N914W-13

## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123



UNIT	A	$b_p$	$c$	D	E	$H_E$	v	$\angle$
mm	1.15 1.05	0.6 0.5	0.135 0.100	2.7 2.6	1.65 1.55	3.85 3.55	0.2	5°

**TOP DYNAMIC**